

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1637	257/355.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:03
L2	366	257/546.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:04
L3	181	257/469.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:05
L4	75	257/633.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:06
L6	268	257/915.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:06
L5	268	257/747.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:07
S10	133	(((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) near10 (absorb\$3 or absorption))) and ("257"/\$.ccls. or "438"/\$.ccls.)) and (diamond or boron?nitride or carbide or carbon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:10
L7	1330	(((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) near10 (absorb\$3 or absorption))) and (diamond or boron?nitride or carbide or carbon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:11
S11	1864	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) near10 (absorb\$3 or absorption))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:14

L8	12350	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) with (resist\$5 or expan\$6))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:16
L9	7040	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) with (resist\$5 or expan\$6)) and (active or channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:16
L10	1141	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) with (resist\$5 or expan\$6)) and ((active or channel) with length)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:16
L11	1136	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((thermal\$3 or heat or thermo?mechanical) with (resist\$5 or expan\$6)) and ((active or channel) with length) and (contact or connect\$ or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:18
L12	575	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and (((thermal\$3 or heat or thermo?mechanical) with (resist\$5 or expan\$6)) same (contact or connect\$ or electrode)) and ((active or channel) with length)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:21
L13	570	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and (((thermal\$3 or heat or thermo?mechanical) with (resist\$5 or expan\$6)) same (contact or connect\$3 or electrode)) and ((active or channel) with length)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:25

L14	1655	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((TiN or (titanium adj nitride) or carbon or c) same (contact or connector or electrode)) and ((active or channel) with length)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:27
L15	1106	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and ((TiN or (titanium adj nitride) or carbon or c) with (contact or connector or electrode)) and ((active or channel) with length)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:27
L16	61	((semiconductor or IC or (integrated adj circuit)) and (ESD or overvoltage or over?voltage or electrostatic or electro?static)) and (((TiN or (titanium adj nitride) or carbon or c) with (contact or connector or electrode)) same ((active or channel) with length))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/16 01:27